

## Charge collection in silicon strips sensors close to the accumulation layer

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The collection of charge carriers injected close to the Si/SiO<sub>2</sub> interface of p on n silicon strip sensors was investigated using a red laser TCT setup. The sensors were investigated non-irradiated and after 1 MGy 12 keV photon irradiation. The relation between charge collection and accumulation layer was studied as well as the dependence on humidity and biasing history. A model of charge collection and charge carrier losses at the interface was developed. Results will be presented and discussed.

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